

**Application No.: 10/644,902****Docket No.: 4425-315****AMENDMENTS TO THE CLAIMS:**

The listing of claims will replace all prior version, and listings, of claims in the application.

**Listing of Claims:****Claims 1-20 (Cancelled)****Claim 21 (new)**

A structure of nonvolatile memory array, comprising:

a substrate;

a plurality of isolation regions in said substrate;

a plurality of gate structures on said substrate;

a buried source line between said plurality of isolation regions, wherein said buried source line is perpendicular to each of said plurality of isolation regions and a depth of said buried source line is less than a depth of said plurality of isolation regions, and wherein the gate structures are not positioned on said buried source line; and

a plurality of drain regions in said substrate.

**Claim 22 (new)**

The structure according to claim 21, wherein each of said plurality of isolation regions is a shallow trench isolation.

**Claim 23 (new)**

The structure according to claim 21, wherein each said plurality of gate structures comprises at least a polysilicon layer.

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Claim 24 (new)

The structure according to claim 21, further comprising a plurality of contacts in said substrate

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